

SOT89 NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

BCX68

ISSUE 3 – FEBRUARY 2007

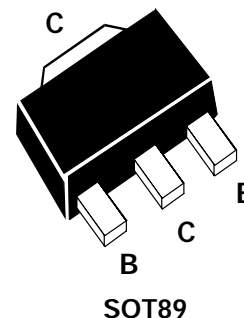


FEATURES

* High gain and low saturation voltages

COMPLEMENTARY TYPE – BCX69

PARTMARKING DETAIL – BCX68 – CE
BCX68-16 – CC
BCX68-25 – CD



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	25	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	1	A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-65 to +150	$^{\circ}C$

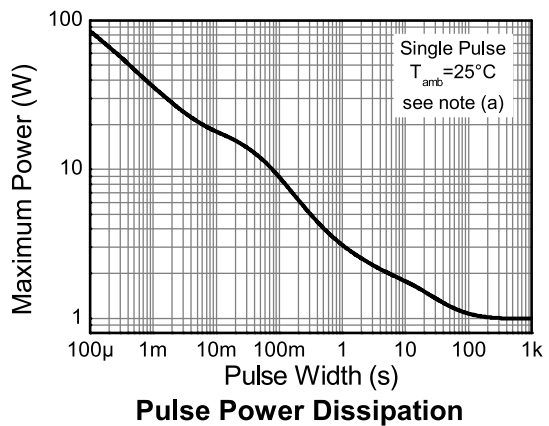
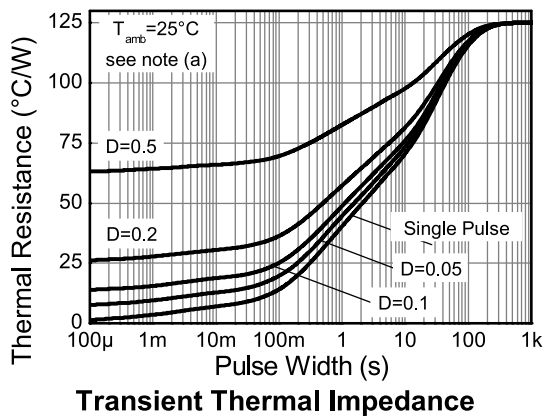
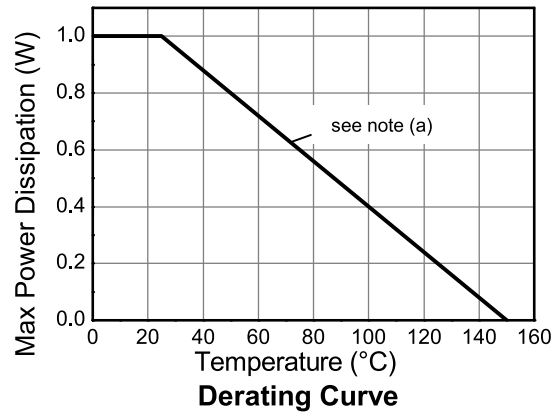
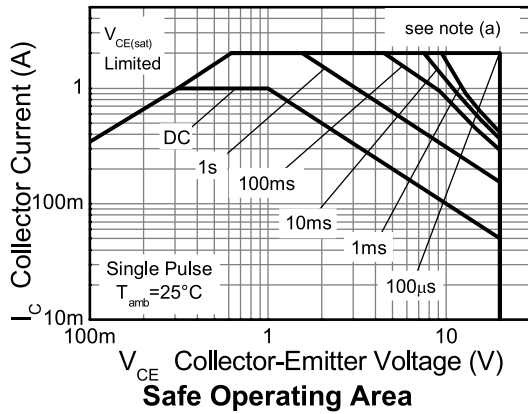
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown voltage	$V_{(BR)CBO}$	25			V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	20			V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E = 100\mu A$
Collector Cut-Off Current	I_{CBO}			0.1 10	μA μA	$V_{CB} = 25V$ $V_{CB} = 25V, T_a = 150^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			10	μA	$V_{EB} = 5V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5	V	$I_C = 1A, I_B = 100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1.0	V	$I_C = 1A, V_{CE} = 1V^*$
Static Forward Current Transfer Ratio	h_{FE}	50 85 60		375		$I_C = 5mA, V_{CE} = 10V$ $I_C = 500mA, V_{CE} = 1V$ $I_C = 1A, V_{CE} = 1V^*$ $I_C = 500mA, V_{CE} = 1V^*$ $I_C = 500mA, V_{CE} = 1V$
Transition Frequency	f_T	100			MHz	$I_C = 100mA, V_{CE} = 5V,$ $f = 100MHz$
Output Capacitance	C_{obo}			25	pF	$V_{CB} = 10V, f = 1MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

BCX68

Characteristics



Note:

- (a) Measured on a 15mm x 15mm x 1.6mm FR4 board with a high coverage of single sided 1oz weight copper.

TYPICAL CHARACTERISTICS

